



Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
60V	22mΩ@10V	20A

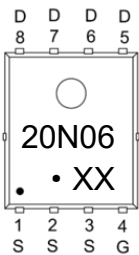
Feature

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high EAS
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power Switching Application
- Hard switched and high frequency circuits
- Uninterruptible Power Supply

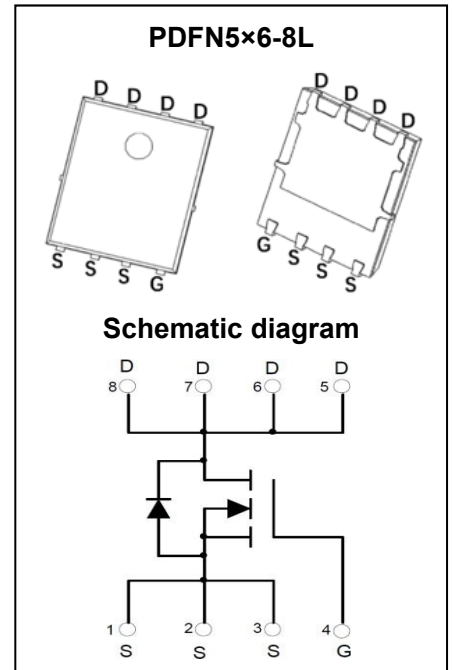
MARKING:



20N06 = Device Code

XX = Date Code

Solid Dot = Green Indicator



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	V_{DS}	60	V
Gate - Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹	$T_C = 25^\circ\text{C}$	I_D	20
	$T_C = 100^\circ\text{C}$	I_D	15
Pulsed Drain Current ²	I_{DM}	60	A
Single Pulsed Avalanche Current ³	I_{AS}	14	A
Single Pulsed Avalanche Energy ³	E_{AS}	49	mJ
Power Dissipation ⁵	$T_C = 25^\circ\text{C}$	P_D	26
Thermal Resistance from Junction to Ambient ⁶	$R_{\theta JA}$	55	$^\circ\text{C/W}$
Thermal Resistance from Junction to Case	$R_{\theta JC}$	4.8	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

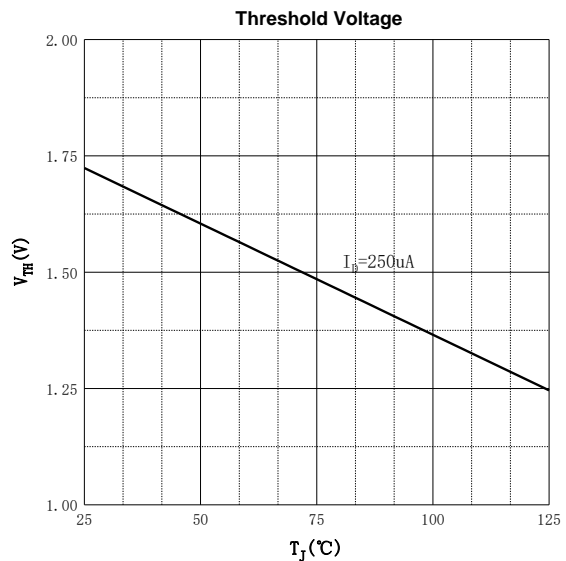
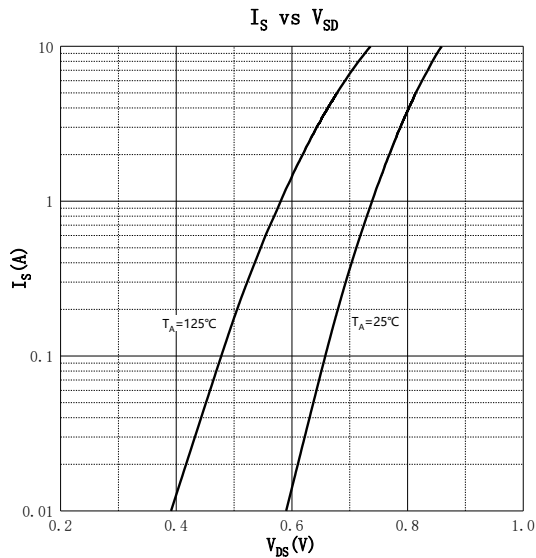
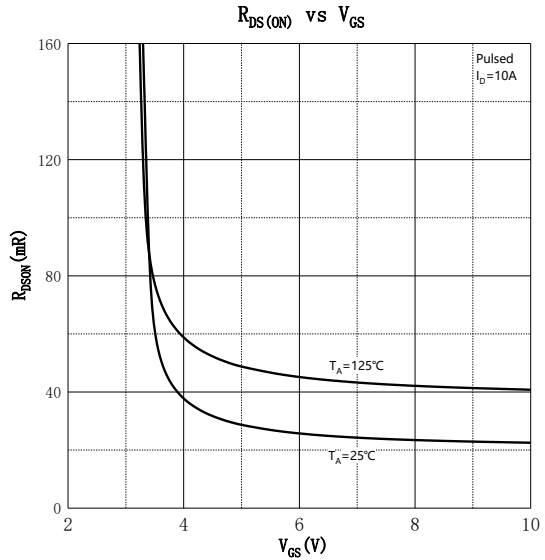
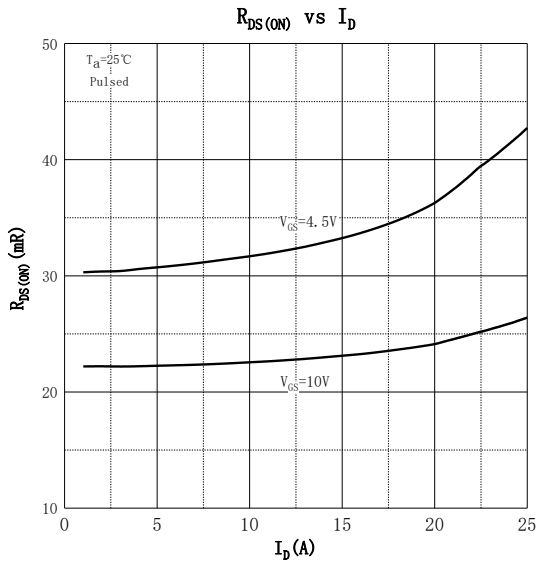
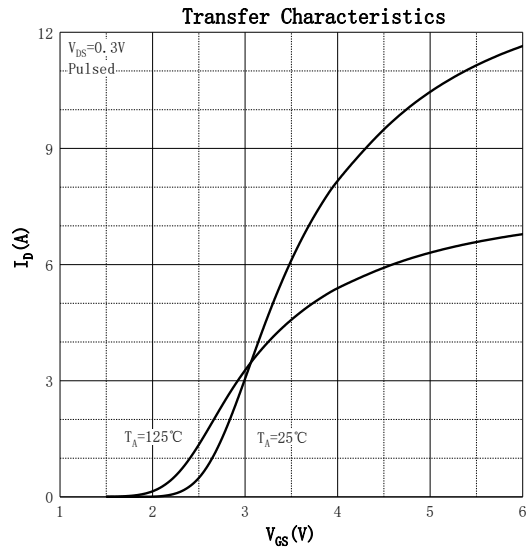
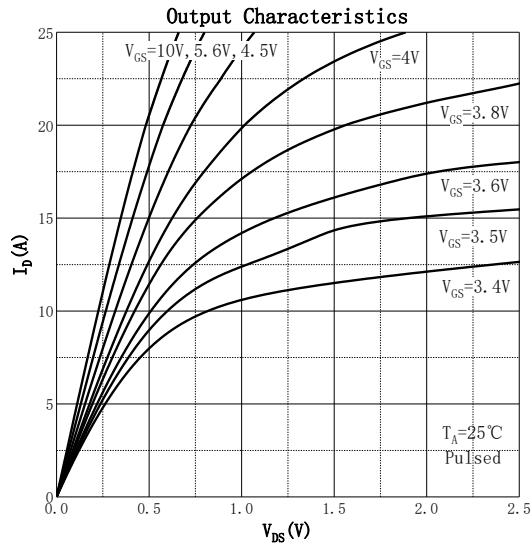
MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60V, V_{GS} = 0V$			1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
On Characteristics⁴						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	1.7	3.0	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 10A$		22	29	m Ω
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 30V, V_{GS} = 0V, f = 1MHz$		888		pF
Output Capacitance	C_{oss}			62		
Reverse Transfer Capacitance	C_{rss}			56		
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = 30V, V_{GS} = 10V, I_D = 10A$		21		nC
Gate-source Charge	Q_{gs}			2.9		
Gate-drain Charge	Q_{gd}			5.6		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 30V, V_{GS} = 10V, R_L = 15\Omega$ $R_G = 2.5\Omega$		5		ns
Turn-on Rise Time	t_r			2.6		
Turn-off Delay Time	$t_{d(off)}$			17		
Turn-off Fall Time	t_f			2.5		
Source - Drain Diode Characteristics						
Diode Forward Voltage ⁴	V_{SD}	$V_{GS} = 0V, I_S = 1A$			1.2	V
Diode Continuous Forward Current ¹	I_S	$T_C = 25^\circ\text{C}$			20	A

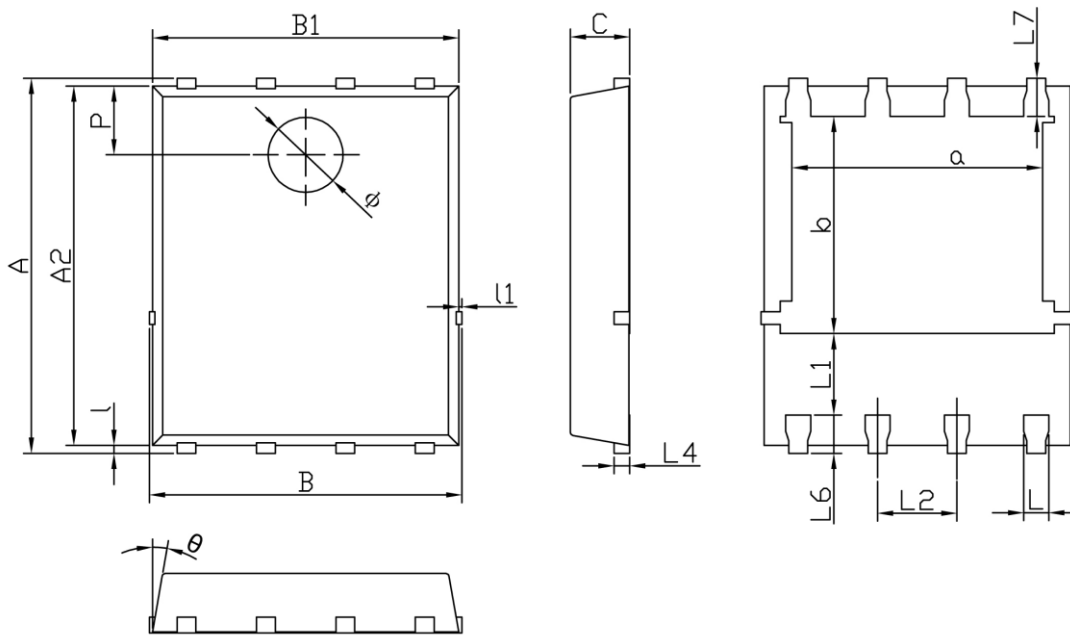
Notes :

- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.EAS condition: $V_{DD} = 30V, V_{GS} = 10V, L = 0.5mH, R_G = 25\Omega$ Starting $T_J = 25^\circ\text{C}$.
- 4.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 5.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.And device mounted on a large heatsink
- 6.Device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics



PDFN5×6-8L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	5.900	6.100	0.232	0.240
a	3.910	4.110	0.154	0.162
A2	5.700	5.800	0.224	0.228
B	4.900	5.100	0.193	0.201
b	3.370	3.570	0.133	0.141
B1	4.800	5.000	0.189	0.197
C	0.900	1.000	0.035	0.039
L	0.350	0.450	0.014	0.018
l	0.060	0.200	0.002	0.008
L1	1.100	-	0.043	-
l1	-	0.100	-	0.004
L2	1.170	1.370	0.046	0.054
L4	0.210	0.340	0.008	0.013
L6	0.510	0.710	0.020	0.028
L7	0.510	0.710	0.020	0.028
P	1.000	1.200	0.039	0.047
Φ	1.100	1.300	0.043	0.051
θ	8°	12°	8°	12°